

August 2015

## FDC658AP

# Single P-Channel Logic Level PowerTrench® MOSFET

-30V, -4A,  $50m\Omega$ 

## **General Description**

This P-Channel Logic Level MOSFET is produced using Fairchild's advanced PowerTrench process. It has been optimized for battery power management applications.

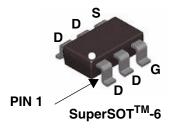
## **Applications**

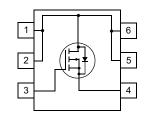
- Battery management
- Load switch
- Battery protection
- DC/DC conversion

### **Features**

- Max  $r_{DS(on)} = 50 \text{ m}\Omega$  @  $V_{GS} = -10 \text{ V}$ ,  $I_D = -4\text{A}$
- Max  $r_{DS(on)} = 75 \text{ m}\Omega$  @  $V_{GS} = -4.5 \text{ V}$ ,  $I_D = -3.4 \text{A}$
- Low Gate Charge
- High performance trench technology for extremely low r<sub>DS(on)</sub>
- RoHS Compliant







## **Absolute Maximum Ratings** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
$V_{DS}$	Drain-Source Voltage		-30	V
$V_{GS}$	Gate-Source Voltage		±25	V
ı	Drain Current - Continuous	(Note 1a)	-4	Α
'D	- Pulsed		-20	_ A
D	Maximum Power dissipation	(Note 1a)	1.6	w
$P_{D}$		(Note 1b)	0.8	] vv
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

## **Package Marking and Ordering Information**

Device Marking	Device	Reel Size	Tape Width	Quantity
.58A	FDC658AP	7inch	8mm	3000 units

Max

Тур

Min

Units

## **Electrical Characteristics** $T_J = 25^{\circ}\text{C}$ unless otherwise noted

Parameter

Off Characteristics							
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0V$	-30			V	
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = -250μA, Referenced to 25°C		-22		mV/°C	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = -24V$			-1	μΑ	
I <sub>GSS</sub>	Gate-Body Leakage	$V_{GS} = \pm 25V, V_{DS} = 0V$			±100	nA	

**Test Conditions** 

### On Characteristics (Note 2)

Symbol

V <sub>GS(TH)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1	-1.8	-3	٧
$\frac{\Delta V_{GS(TH)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\mu A$ , Referenced to 25°C		4		mV/°C
		$I_D = -4A, V_{GS} = -10V$		44	50	
r ·	Static Drain-Source On-Resistance	$I_D = -3.4A, V_{GS} = -4.5V$		67	75	mΩ
r <sub>DS(on)</sub>	Statio Brain Goards On Heddidands	$I_D = -4A$ , $V_{GS} = -10V$ , $T_J = 125$ °C		60	70	11132
I <sub>D(ON)</sub>	On-State Drain Current	$V_{GS} = -10V, V_{DS} = -5V$	-20			Α
9 <sub>FS</sub>	Forward Transconductance	$I_D = -4A, V_{DS} = -5V$		8.4		S

### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 45V V 0V	470	680	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz	126	180	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 – 111112	61	90	pF

### **Switching Characteristics** (Note 2)

t <sub>d(on)</sub>	Turn-On Delay Time		7	14	ns
t <sub>r</sub>	Turn-On Rise Time	V <sub>DD</sub> = -15V, I <sub>D</sub> = -1A	12	22	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = -10V, R_{GEN} = 6\Omega$	16	29	ns
t <sub>f</sub>	Turn-Off Fall Time		6	12	ns
$Q_g$	Total Gate Charge	V 45V L 44	6	8.1	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS} = -15V, I_{D} = -4A,$ $V_{GS} = -5V$	2.1		nC
Q <sub>gd</sub>	Gate-Drain Charge	▼GS = -3 V	2		nC

## **Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current			-1.3	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0V$ , $I_S = -1.3$ A (Note 2)	-0.77	-1.2	V

#### Notes:

<sup>1:</sup> R<sub>0,JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>0,JC</sub> is guaranteed by design while R<sub>0,CA</sub> is determined by the user's board design.



a) 78°C/W when mounted on a 1 in² pad of 2 oz copper



b) 156°C/W whe mounted on a minimum pad of 2 oz copper

Scale 1: 1 on letter size paper

2: Pulse Test: Pulse Width < 300  $\mu$ s, Duty Cycle < 2.0%

## **Typical Characteristics**

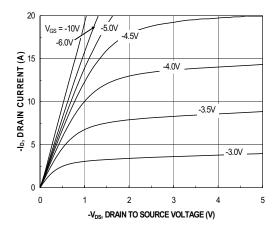


Figure 1. On-Region Characteristics

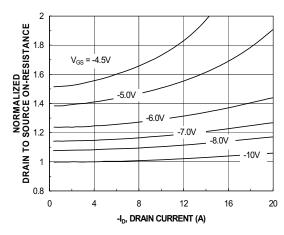


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

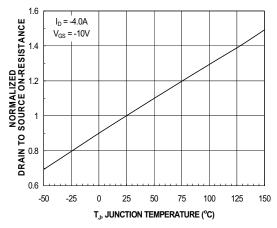


Figure 3. Normalized On-Resistance vs Junction Temperature

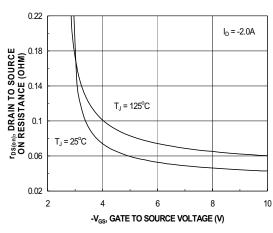


Figure 4. On-Resistance vs Gate to Source Voltage

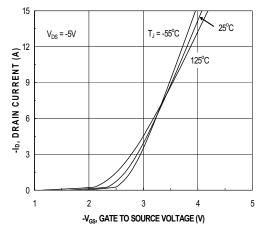


Figure 5. Transfer Characteristics

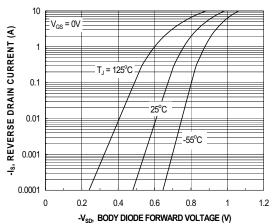
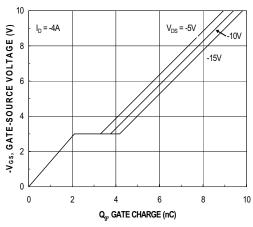


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

## **Typical Characteristics**



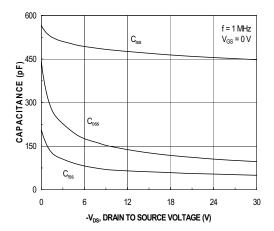
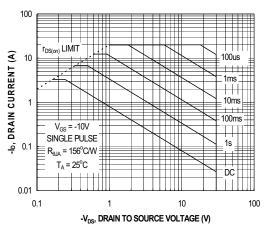


Figure 7. Gate Charge Characteristics

Figure 8. Capacitance vs Drain to Source Voltage



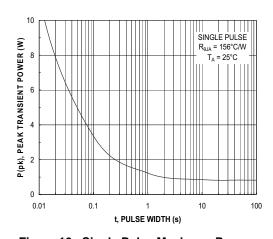


Figure 9. Forward Bias Safe Operating Area

Figure 10. Single Pulse Maximum Power Dissipation

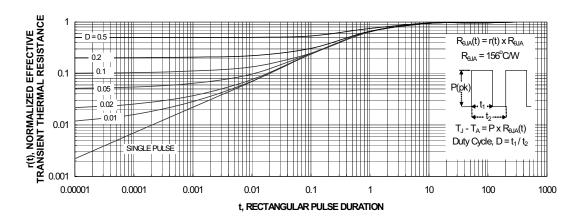


Figure 11. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.





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